

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	SPD30P06PG
▶ Overseas	Part Number	SPD30P06PG
▶ Equivalent	Part Number	SPD30P06PG

EV is the abbreviation of name EVVO

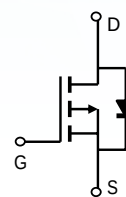
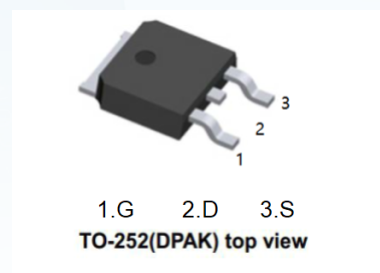
-60V P-Channel MOSFET

Features

- P-Channel
- Enhancement mode
- Avalanche rated
- dv/dt rated
- 175°C operating temperature

Product Summary

- $V_{DS}(V) = -60V$
- $R_{DS(on)} = 75\text{ m}\Omega$ ($V_{GS} = -10V$)
- $I_D = -30A$ ($V_{GS} = -10V$)



Maximum Ratings, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ }^\circ\text{C}$ $T_C = 100\text{ }^\circ\text{C}$	I_D	-30 -21.5	A
Pulsed drain current $T_C = 25\text{ }^\circ\text{C}$	$I_{D\text{ puls}}$	-120	
Avalanche energy, single pulse $I_D = -30\text{ A}$, $V_{DD} = -25\text{ V}$, $R_{GS} = 25\text{ }\Omega$	E_{AS} mJ	250	mJ
Avalanche energy, periodic limited by T_{jmax}	E_{AR}	12.5	
Reverse diode dv/dt $I_S = -30\text{ A}$, $V_{DS} = -48\text{ V}$, $di/dt = 200\text{ A}/\mu\text{s}$, $T_{jmax} = 175\text{ }^\circ\text{C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_C = 25\text{ }^\circ\text{C}$	P_{tot} W	125	W
Operating and storage temperature	T_j, T_{stg}	-55+175	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/175/56	

-60V P-Channel MOSFET

Thermal Characteristics

Parameter	Symbol		Values		Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R _{thJC}			1.2	K/W
Thermal resistance, junction - ambient, leaded	R _{thJA}			100	
SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ¹⁾	R _{thJA}			75 50	
Electrical Characteristics, at T _j = 25 °C, unless otherwise specified					
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage V _{GS} = 0 V, I _D = -250 μA	V _{(BR)DSS}	-60			V
Gate threshold voltage, V _{GS} = V _{DS} I _D = -1.7 mA	V _{GS(th)}	-2.1	-3	-4	
Zero gate voltage drain current V _{DS} = -60 V, V _{GS} = 0 V, T _j = 25 °C V _{DS} = -60 V, V _{GS} = 0 V, T _j = 150 °C	I _{DSS}		-0.1 -10	-1 -100	μA
Gate-source leakage current V _{GS} = -20 V, V _{DS} = 0 V	I _{GSS}		-10	-100	
Drain-source on-state resistance V _{GS} = -10 V, I _D = -21.5 A	R _{DS(on)}		69	75	mΩ

-60V P-Channel MOSFET

Electrical Characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
Dynamic Characteristics		min.	typ.	max.	
Transconductance $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = -21.5\text{ A}$	g_{fs}	5.2	10.4		S
Input capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1\text{ MHz}$	C_{iss}		1228	1535	pF
Output capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1\text{ MHz}$	C_{oss}		387	383	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1\text{ MHz}$	C_{rss}		142	177	
Turn-on delay time $V_{DD} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -21.5\text{ A}$, $R_G = 1.6\text{ }\Omega$	$t_{d(on)}$		13	19.5	ns
Rise time $V_{DD} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -21.5\text{ A}$, $R_G = 1.6\text{ }\Omega$	t_r		11	16.5	
Turn-off delay time $V_{DD} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -21.5\text{ A}$, $R_G = 1.6\text{ }\Omega$	$t_{d(off)}$		30	45	
Fall time $V_{DD} = -30\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -21.5\text{ A}$, $R_G = 1.6\text{ }\Omega$	t_f		20	30	

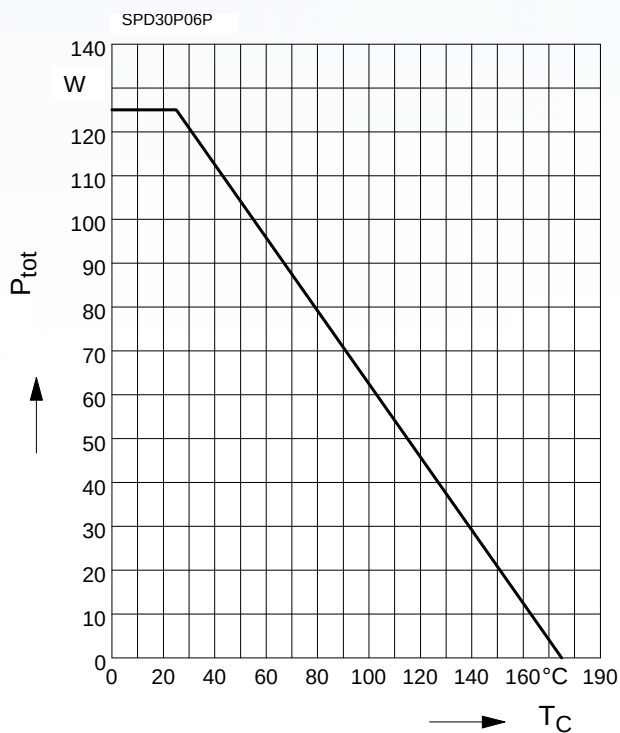
-60V P-Channel MOSFET

Electrical Characteristics, at $T_j = 25\text{ }^{\circ}\text{C}$, unless

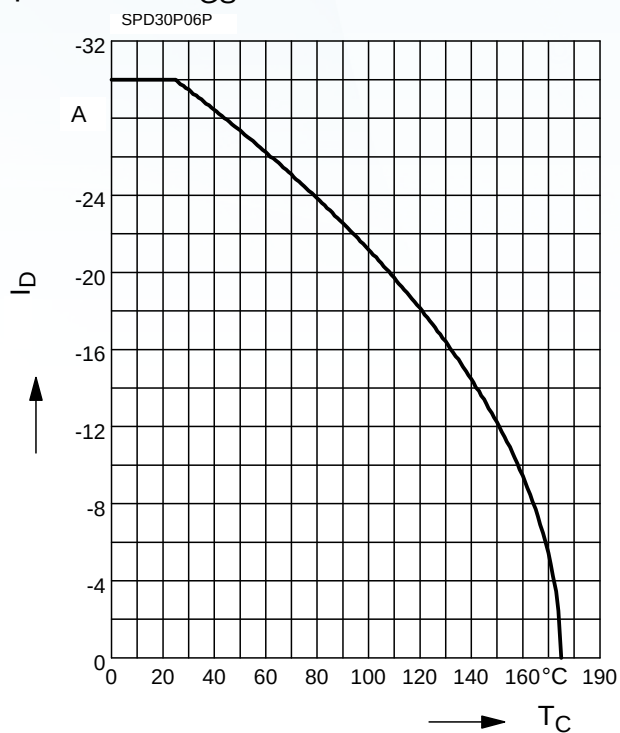
Parameter	Symbol		Values		Unit
		min.	typ.	max.	
Dynamic Characteristics					
Gate to source charge V _{DD} = -48 V, I _D = -30 A	Q _{gs}		3.7	5.6	nC
Gate to drain charge V _{DD} = -48 V, I _D = -30 A	Q _{gd}		13.8	20.7	
Gate charge total V _{DD} = -48 V, I _D = -30 A, V _{GS} = 0 to -10 V	Q _g		32	48	
Gate plateau voltage V _{DD} = -48 V , I _D = -30 A	V _(plateau)		-5.2		V
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current T _C = 25 °C	I _S			-30	A
Inverse diode direct current,pulsed T _C = 25 °C	I _{SM}			-120	
Inverse diode forward voltage V _{GS} = 0 V, I _F = -30	V _{SD}		-1.3	-1.7	V
Reverse recovery time V _R = -30 V, I _F =I _S , di _F /dt = 100 A/μs	t _{rr}		64.6	97	ns
Reverse recovery charge V _R = -30 V, I _F =I _S , di _F /dt = 100 A/μs	Q _{rr}		153	230	nC

-60V P-Channel MOSFET
Power dissipation

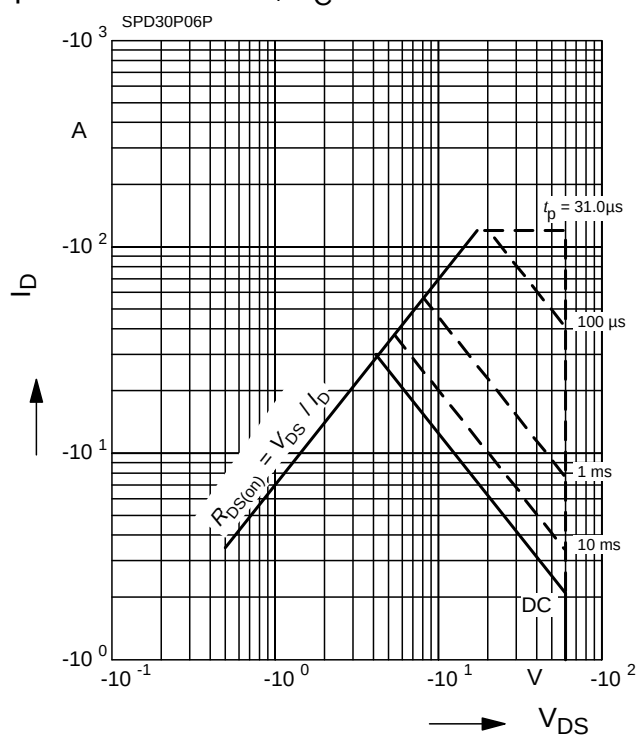
$$P_{\text{tot}} = f(T_C)$$


Drain current

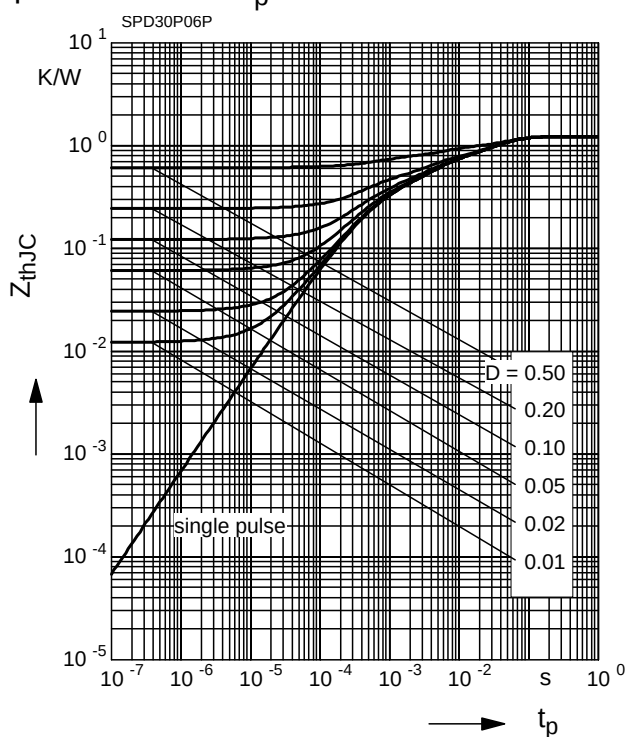
$$I_D = f(T_C)$$

 parameter: $V_{GS} \geq 10 \text{ V}$

Safe operating area

$$I_D = f(V_{DS})$$

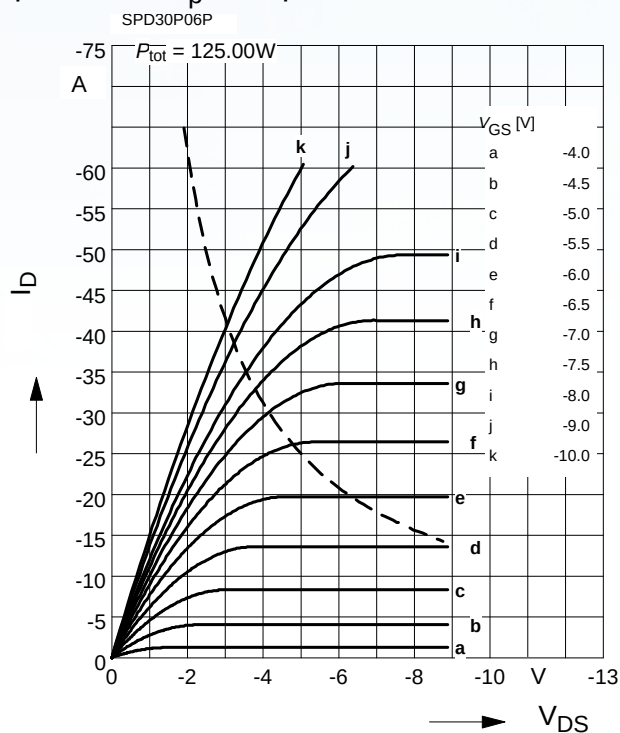
 parameter : $D = 0$, $T_C = 25^{\circ}\text{C}$

Transient thermal impedance

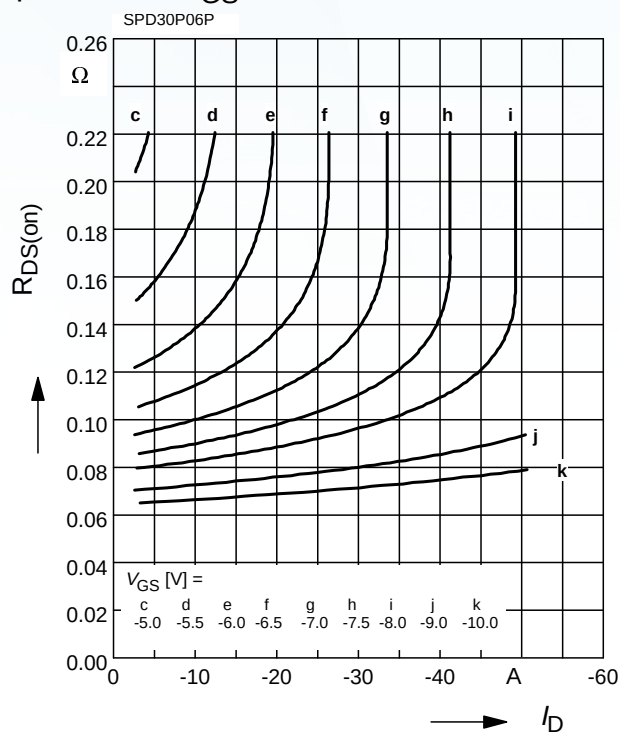
$$Z_{\text{thJC}} = f(t_p)$$

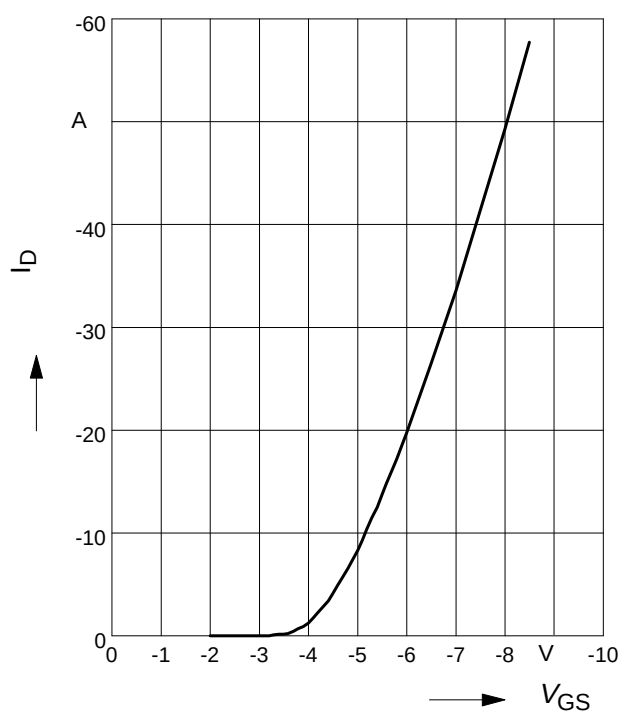
 parameter : $D = t_p / T$


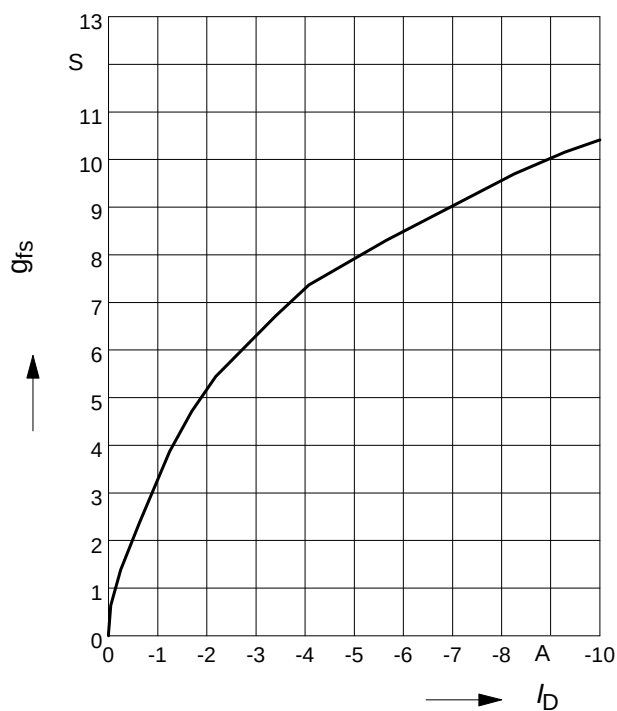
-60V P-Channel MOSFET

Typ. output characteristic
 $I_D = f(V_{DS}); T_J = 25^\circ\text{C}$

 parameter: $t_p = 80\ \mu\text{s}$
**Typ. drain-source-on-resistance**
 $R_{DS(\text{on})} = f(I_D)$

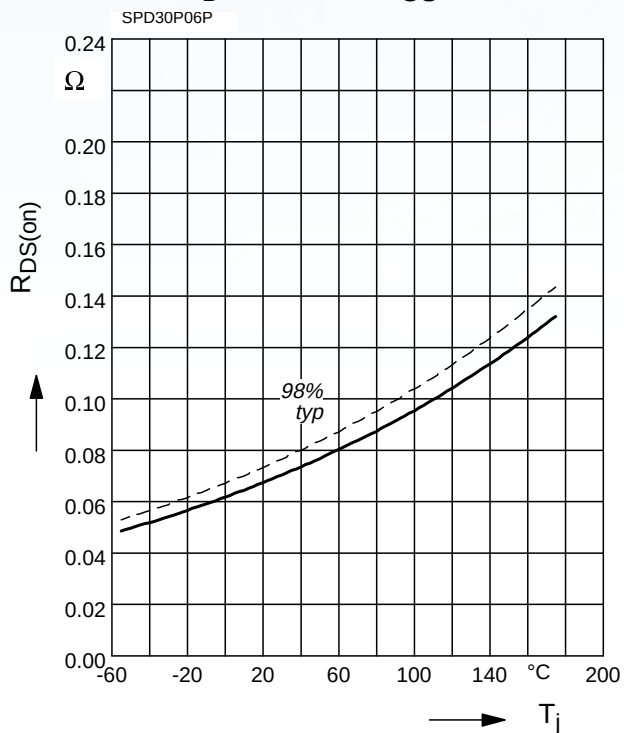
 parameter: V_{GS}
**Typ. transfer characteristics $I_D = f(V_{GS})$**
 $V_{DS} \geq 2 \times I_D \times R_{DS(\text{on})\text{max}}$

 parameter: $t_p = 80\ \mu\text{s}$
**Typ. forward transconductance**
 $g_{fs} = f(I_D); T_J = 25^\circ\text{C}$

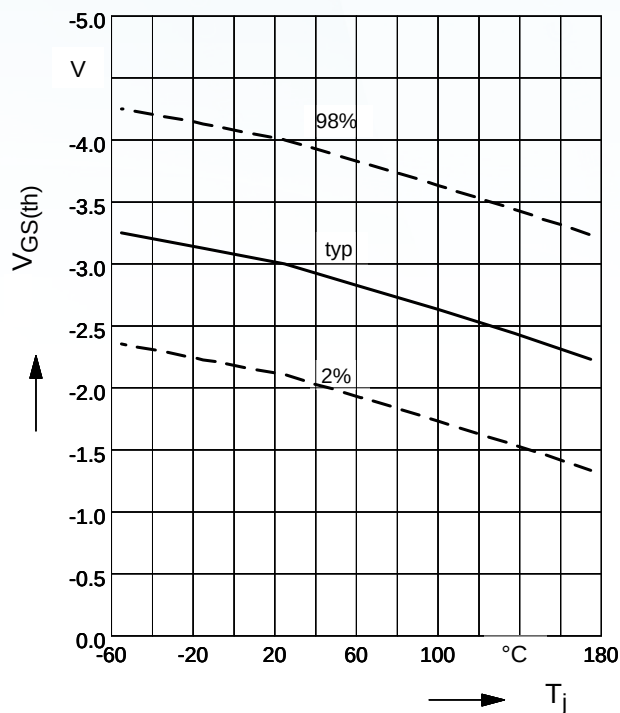
 parameter: g_{fs}


-60V P-Channel MOSFET
Drain-source on-state resistance

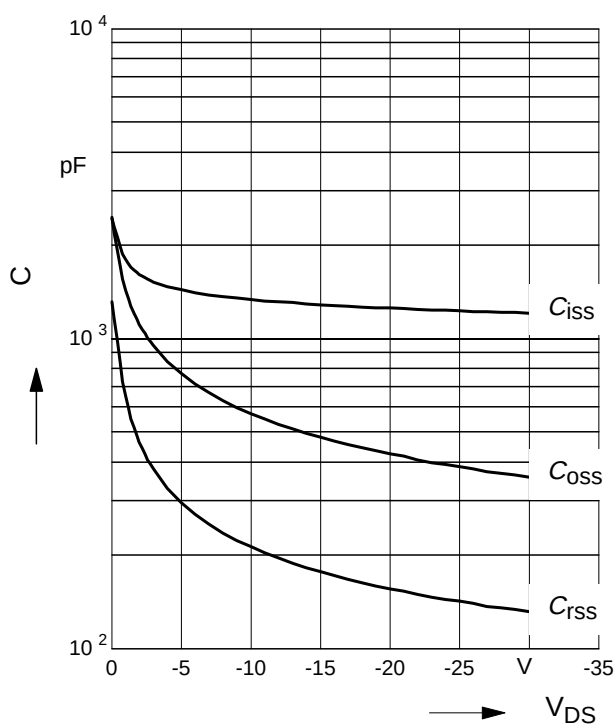
$$R_{DS(on)} = f(T_j)$$

 parameter : $I_D = -21.5\text{ A}$, $V_{GS} = -10\text{ V}$

Gate threshold voltage

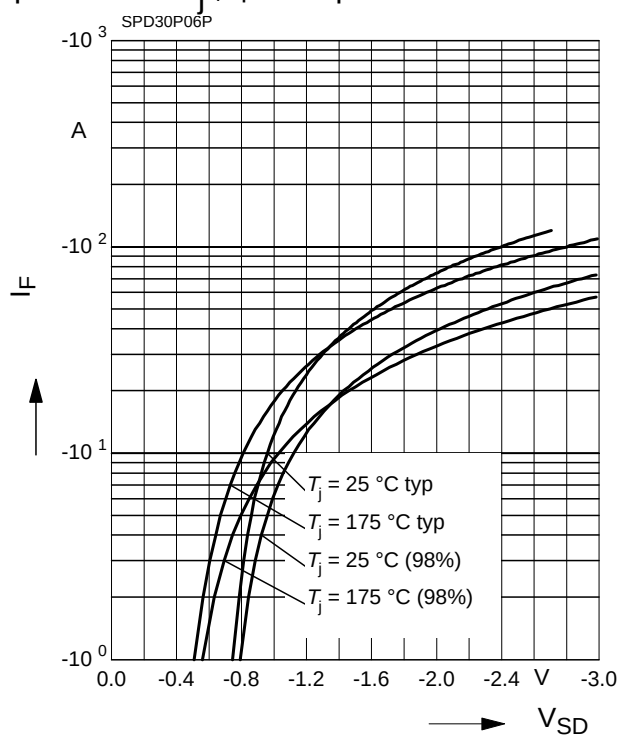
$$V_{GS(th)} = f(T_j)$$

 parameter: $V_{GS} = V_{DS}$, $I_D = -1.7\text{ mA}$

Typ. capacitances

$$C = f(V_{DS})$$

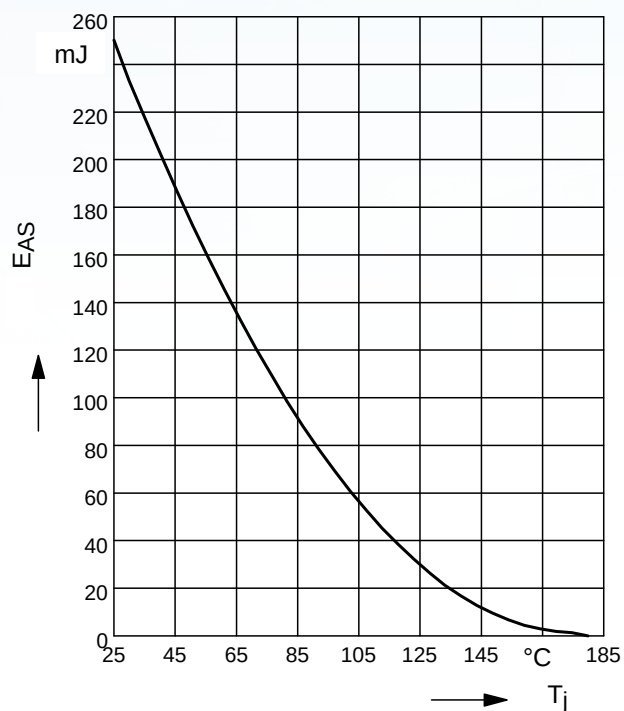
 parameter: $V_{GS}=0\text{V}$, $f=1\text{ MHz}$

Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

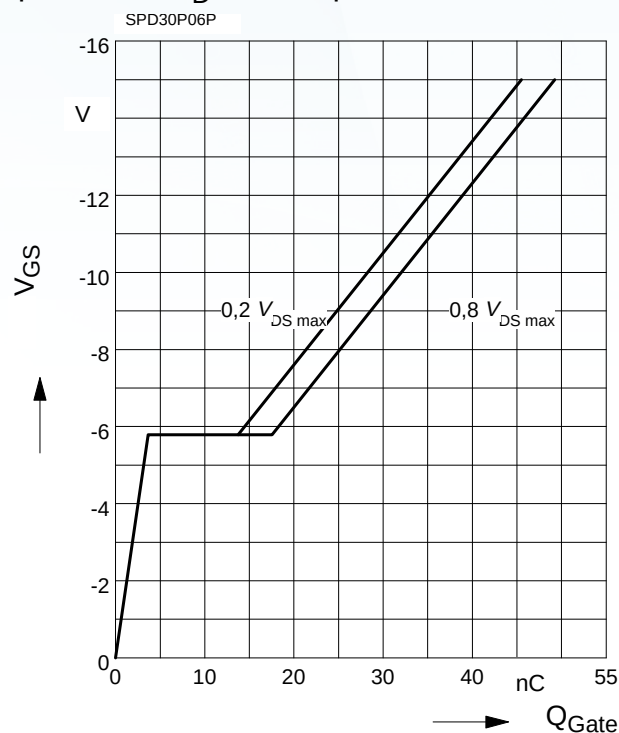
 parameter: T_j , $t_p = 80\text{ }\mu\text{s}$


-60V P-Channel MOSFET
Avalanche energy

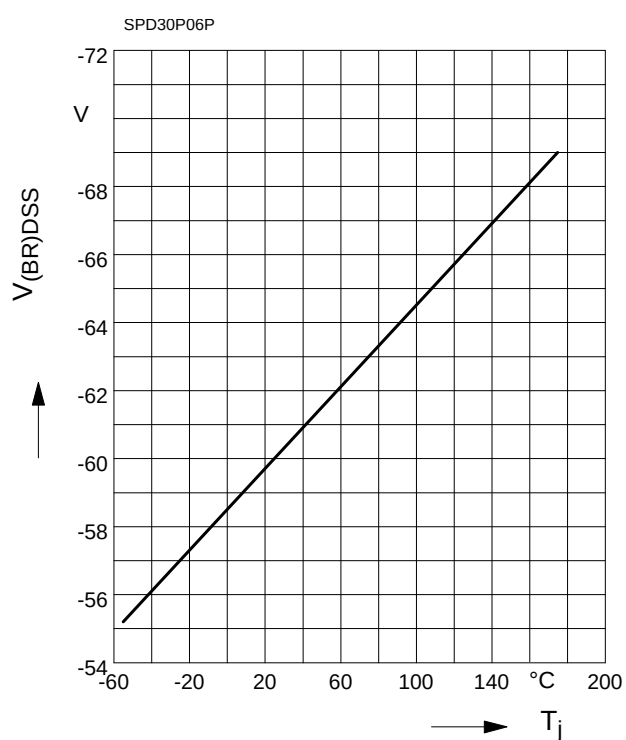
$$E_{AS} = f(T_j)$$

 para.: $I_D = -30\text{ A}$, $V_{DD} = -25\text{ V}$, $R_{GS} = 25\ \Omega$

Typ. gate charge

$$V_{GS} = f(Q_{\text{Gate}})$$

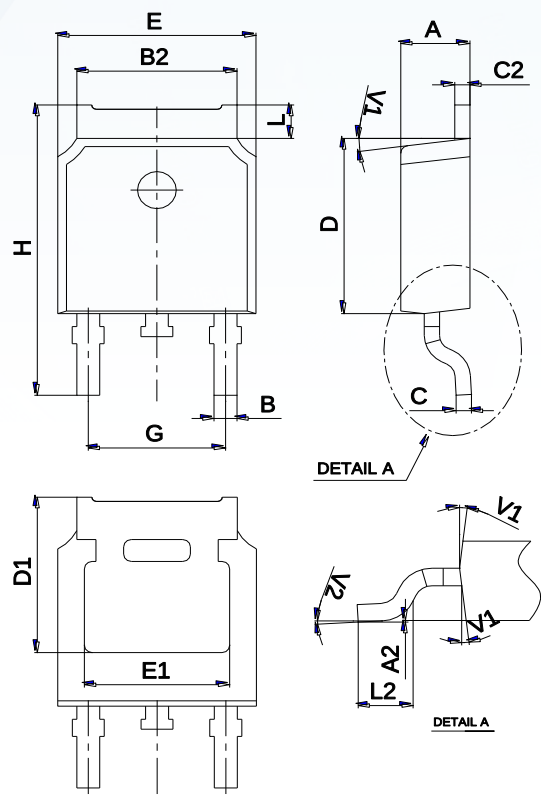
 parameter: $I_D = -30\text{ A}$ pulsed

Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$



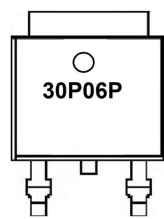
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Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
SPD30P06PG	TO-252	2500	Tape and reel

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